

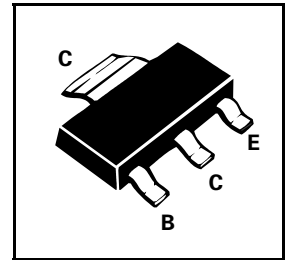
SOT223 PNP SILICON PLANAR SWITCHING TRANSISTOR

ISSUE 4 – JUNE 1996



FZT4403

PARTMARKING DETAIL – FZT4403



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-600	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1.5	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		V	$I_C = -0.1mA$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	$I_C = -1mA$
Emitter Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -0.1mA$
Base Cut-off Current	I_{BEX}		-0.1	μA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
Collector-Emitter Cut-off Current	I_{CEX}		-0.1	μA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.4 -0.75	V	$I_C = -150mA, I_B = -15mA^*$ $I_C = -500mA, I_B = -50mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.75	-0.95 -1.3	V	$I_C = -150mA, I_B = -15mA^*$ $I_C = -500mA, I_B = -50mA^*$
Static Forward Current Transfer Ratio	h_{FE}	30 60 100 100 20	300		$I_C = -0.1mA, V_{CE} = -1V$ $I_C = -1mA, V_{CE} = -1V$ $I_C = -10mA, V_{CE} = -1V$ $I_C = -150mA, V_{CE} = -2V^*$ $I_C = -500mA, V_{CE} = -2V^*$
Transition Frequency	f_T	200		MHz	$I_C = -50mA, V_{CE} = -5V$ $f = 100MHz$
Output Capacitance	C_{obo}		8.5	pF	$V_{CB} = -10V, f = 100KHz$ $I_E = 0$
Input Capacitance	C_{ibo}		30	pF	$I_C = 0, f = 100kHz$

*Measured under pulsed conditions. Pulse width=300 μs .